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FDA18N50 N-Channel UniFET[™] MOSFET 500 V, 19 A, 265 mΩ

Features

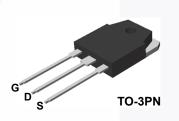
- $R_{DS(on)}$ = 265 m Ω (Max.) @ V_{GS} = 10 V, I_D = 9.5 A
- Low Gate Charge (Typ. 45 nC)
- Low C_{rss} (Typ. 25 pF)
- 100% Avalanche Tested

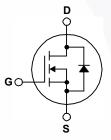
Applications

- PDP TV
- Uninterruptible Power Supply
- AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDA18N50	Unit	
V _{DSS}	Drain-Source Voltage			500	V	
ID	Drain Current	- Continuous ($T_C = 25^{\circ}C$) - Continuous ($T_C = 100^{\circ}C$)		19 11.4	A A	
I _{DM}	Drain Current	- Pulsed	(Note 1)	76	А	
V _{GSS}	Gate-Source voltage			±30	V	
E _{AS}	Single Pulsed Avalanche Energy		(Note 2)	945	mJ	
I _{AR}	Avalanche Current		(Note 1)	19	А	
E _{AR}	Repetitive Avalanche Energy		(Note 1)	23	mJ	
dv/dt	Peak Diode Recovery dv/dt		(Note 3)	4.5	V/ns	
P _D	Power Dissipation	(T _C = 25°C) - Derate above 25°C		239 1.92	W W/°C	
T _{J,} T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C		
TL	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		300	°C		

Thermal Characteristics

Symbol	Parameter	FDA18N50	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction-to-Case, Max.	0.52	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	C/W	

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N-Channel UniFET ^{1M} MOSFET	Unit V V/°C μΑ μΑ nA nA N Ω S	
SFET	V Ω	
		S
		pF
		pF
		pF

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDA18N50	FDA18N50	TO-3PN	Tube	N/A	30 units

Electrical Characteristics $T_{C} = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter Conditions		Min.	Тур.	Max	Unit
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_{D} = 250\mu A$				V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	$I_D = 250\mu A$, Referenced to $25^{\circ}C$		0.5		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 500V, V_{GS} = 0V$ $V_{DS} = 400V, T_{C} = 125^{\circ}C$			1 10	μΑ μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 9.5A		0.220	0.265	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40V, I _D = 9.5A		25		S
Dynamic C	Characteristics				1	
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz		2200	2860	pF
C _{oss}	Output Capacitance			330	430	pF
C _{rss}	Reverse Transfer Capacitance	_		25	40	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 250V, I _D = 19A		55	120	ns
t _r	Turn-On Rise Time	$R_{G} = 25\Omega$		165	340	ns
t _{d(off)}	Turn-Off Delay Time		-	95	200	ns
t _f	Turn-Off Fall Time	(Note 4)		90	190	ns
Qg	Total Gate Charge	V _{DS} = 400V, I _D = 19A		45	60	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10V		12.5		nC
Q _{gd}	Gate-Drain Charge	(Note 4)		19		nC
Drain-Sour	rce Diode Characteristics and Maximur	n Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				19	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current				76	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 19A			1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 19A		500		ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt =100A/μs		5.4		μC

NOTES:

1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. L = 4.7mH, I_{AS} = 19A, V_DD = 50V, R_G = 25 Ω , Starting T_J = 25°C

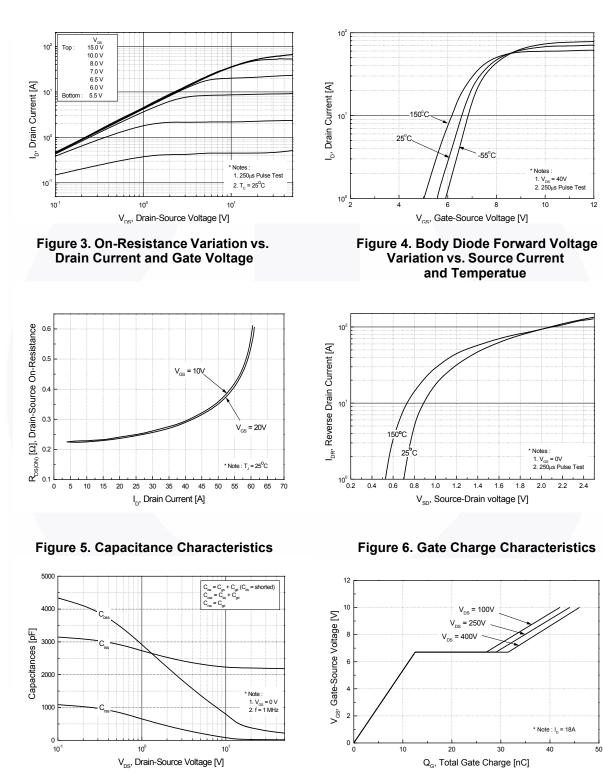
3. I_{SD} \leq 19A, di/dt \leq 200A/µs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C

4. Essentially Independent of Operating Temperature Typical Characteristics

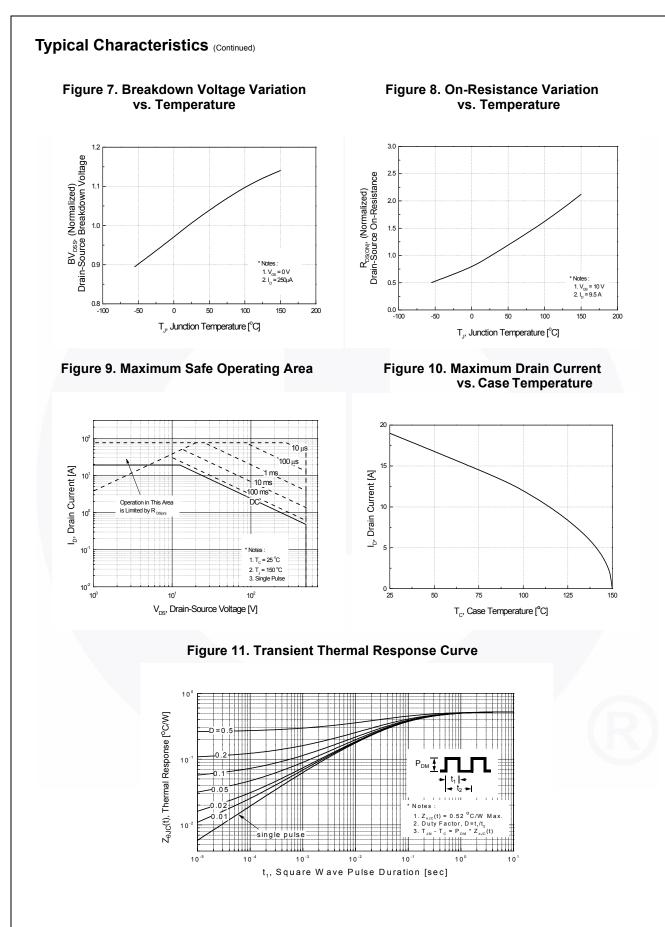
Typical Characteristics



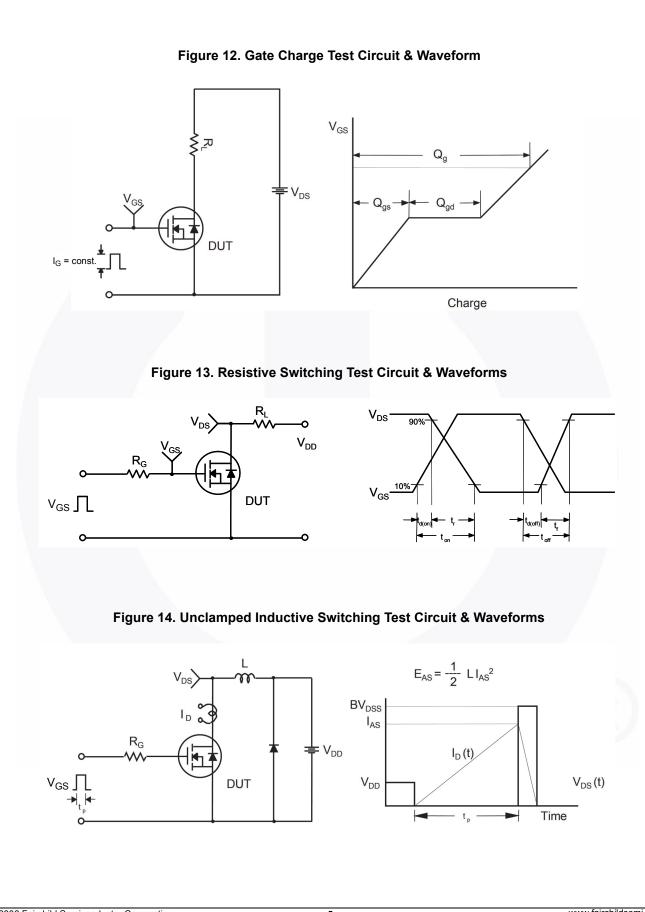
Figure 2. Transfer Characteristics



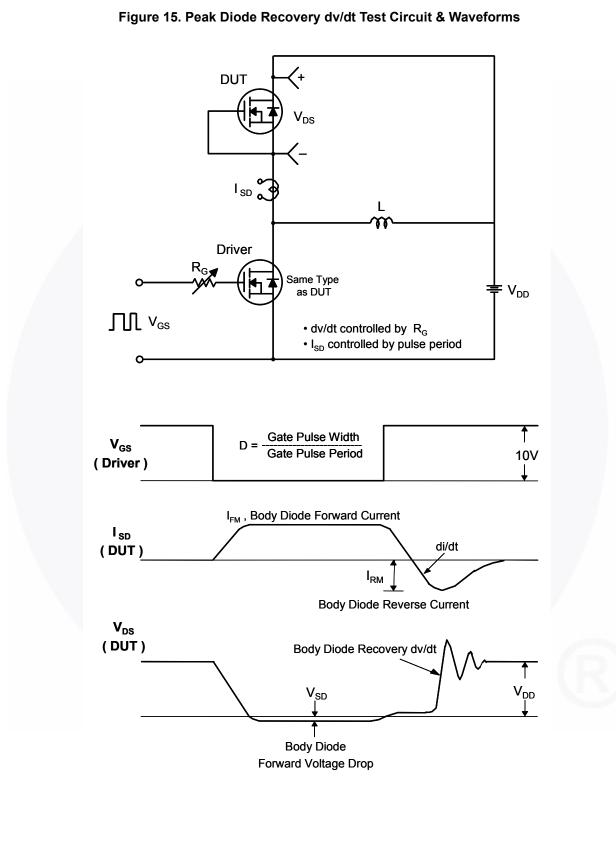
FDA18N50 — N-Channel UniFETTM MOSFET

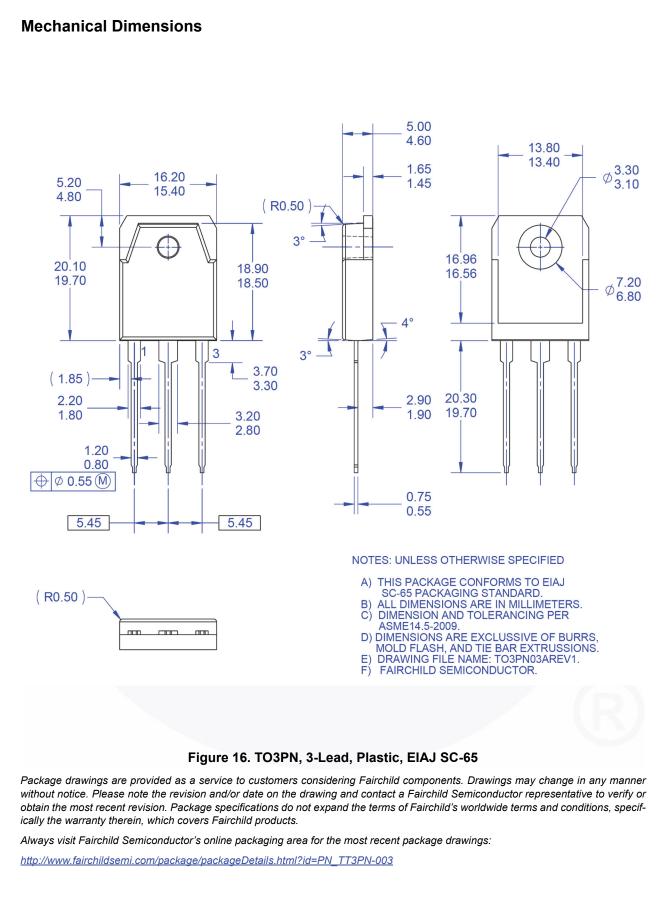


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